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## NTE2637 Silicon NPN Transistor CRT Horizontal Deflection, High Voltage, Fast Switching TO3P Full Pack

**Features:**

- High Breakdown Voltage Capability
- Fully Insulated Package for Easy Mounting
- Low Saturation Voltage
- High Switching Speed

**Applications:**

- Horizontal Deflection Stage in Standard and High Resolution Displays for TVs and Monitors
- Switching Power Supply for TVs and Monitors

**Absolute Maximum Ratings:**

Collector-Base Voltage ( $I_E = 0$ ), $V_{CBO}$ .....	1700V
Collector-Emitter Voltage ( $I_B = 0$ ), $V_{CEO}$ .....	700V
Emitter-Base Voltage ( $I_C = 0$ ), $V_{EBO}$ .....	10V
Collector Current, $I_C$	
Continuous .....	8A
Peak ( $t_p < 5ms$ ) .....	15A
Base Current, $I_B$	
Continuous .....	5A
Peak ( $t_p < 5ms$ ) .....	8A
Total Dissipation ( $T_C = +25^\circ C$ ), $P_{tot}$ .....	60W
Maximum Operating Junction Temperature, $T_J$ .....	+150°C
Storage Temperature Range, $T_{stg}$ .....	-65° to +150°C
Maximum Thermal Resistance, Junction-to-Case, $R_{thJC}$ .....	2.08°C/W

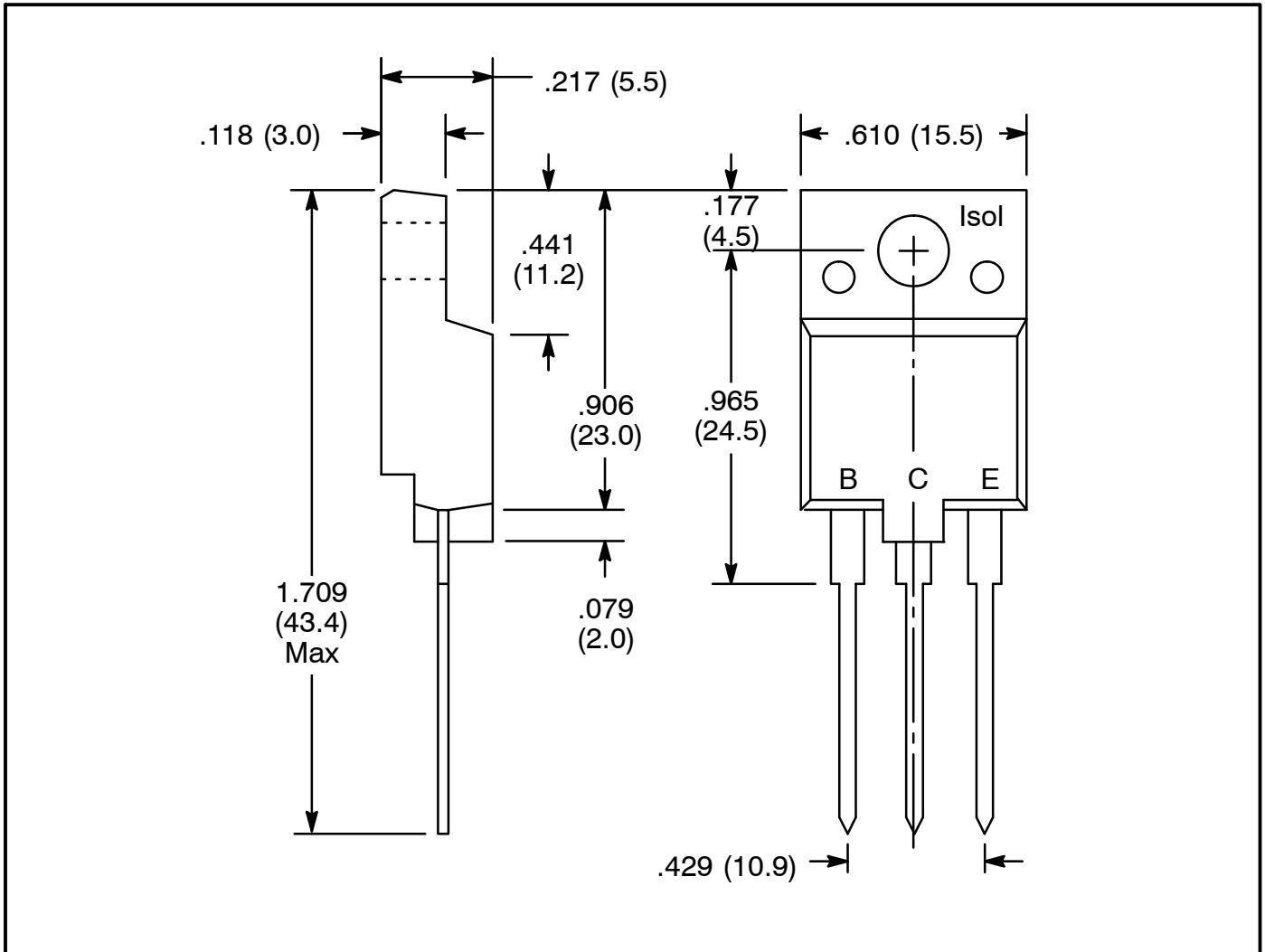
**Electrical Characteristics:** ( $T_C = +25^\circ C$  unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit	
Collector Cutoff Current	$I_{CES}$	$V_{CE} = 1700V,$ $V_{BE} = 0$		-	-	1	mA
			$T_J = +125^\circ C$	-	-	2	mA
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = 5V, I_C = 0$	-	-	100	µA	

**Electrical Characteristics (Cont'd):** ( $T_C = +25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector–Emitter Sustaining Voltage	$V_{CEO(sus)}$	$I_C = 100\text{mA}$	700	–	–	V
Emitter–Base Voltage	$V_{EBO}$	$I_E = 10\text{mA}, I_C = 0$	10	–	–	V
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 5\text{A}, I_B = 1.25\text{A}$ , Note 1	–	–	1.5	V
Base–Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 5\text{A}, I_B = 1.25\text{A}$ , Note 1	–	–	1.3	V
DC Current Gain	$h_{FE}$	$I_C = 5\text{A}, V_{CE} = 5\text{V}$ , Note 1	6	–	–	
			$T_J = +100^\circ\text{C}$	4	–	–
<b>Resistive Load</b>						
Storage Time	$t_s$	$V_{CC} = 400\text{V}, I_C = 5\text{A}, I_{B1} = 1.25\text{A},$ $I_{B2} = 2.5\text{A}$	–	2.7	3.9	$\mu\text{s}$
Fall Time	$t_f$		–	190	280	ns
<b>Resistive Load</b>						
Storage Time	$t_s$	$I_C = 5\text{A}, f = 15625\text{Hz}, I_{B1} = 1.25\text{A},$ $I_{B2} = 2.5\text{A},$ $V_{ceflyback} = 1050 \sin(\pi/10 \cdot 10^6)t \text{ V}$	–	2.3	–	$\mu\text{s}$
Fall Time	$t_f$		–	350	–	ns
Storage Time	$t_s$	$I_C = 5\text{A}, f = 31250\text{Hz}, I_{B1} = 1.25\text{A},$ $I_{B2} = 2.5\text{A},$ $V_{ceflyback} = 1200 \sin(\pi/10 \cdot 10^6)t \text{ V}$	–	2.3	–	$\mu\text{s}$
Fall Time	$t_f$		–	200	–	ns

Note 1. Pulsed: Pulse Duration = 300 $\mu\text{s}$ , Duty Cycle = 1.5%.



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